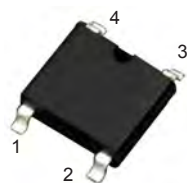


BRIDGE RECTIFIER



DBS Package

PINNING

PIN	DESCRIPTION
1	Input Pin (~)
2	Input Pin (~)
3	Output Anode (+)
4	Output Cathode (-)

Features

- Glass Passivated Chip Junction
- Reverse Voltage - 1000 V
- Forward Current - 1A
- High Surge Current Capability
- Designed For Surface Mount Application

Benefits

- Case: DBS
- Terminals: Solderable Per MIL-STD-750
- Approx. Weight: 0.234g / 0.00825oz

Maximum Ratings and Electrical characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.

Parameter	Symbols	DB107S	Units
Maximum Repetitive Peak Reverse Voltage	VRRM	1000	V
Maximum RMS voltage	VRMS	700	V
Maximum DC Blocking Voltage	VDC	1000	V
Average Rectified Output Current	Io	1.0	A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	IFSM	40	A
I ² t rating for fusing (1ms< t < 8.3ms)	I ² t	6.6	A ² S
Maximum Forward Voltage at 0.5 A	VF	1.0	V
Maximum DC Reverse Current @TA=25 °C at Rated DC Blocking Voltage @TA=125 °C	IR	5 100	μA
Typical Junction Capacitance (Note1)	Cj	32	pF
Operating and Storage Temperature Range	Tj, Tstg	-55 ~ +150	°C
Typical thermal resistance (Note 2)	RthJC	16	°C/W

Note: 1. Measured at 1MHz and applied reverse voltage of 4 VDC.

2. Thermal resistance from Junction to case, lead and ambient in accordance with JESD-51. Unit mounted on 15mm*12mm*1.6mm AL pad attach 195mm*195mm*10mm steel plate

RATINGS AND CHARACTERISTICS CURVES (TA = 25 °C unless otherwise noted)

FIG1:Io-Ta Curve

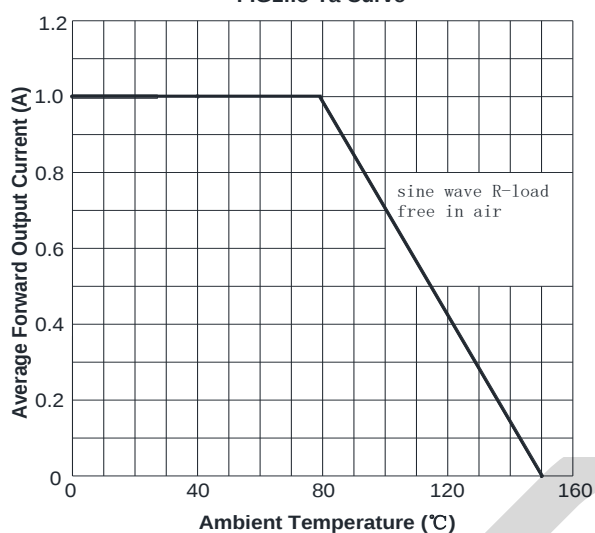


FIG2: Surge Forward Current Capability

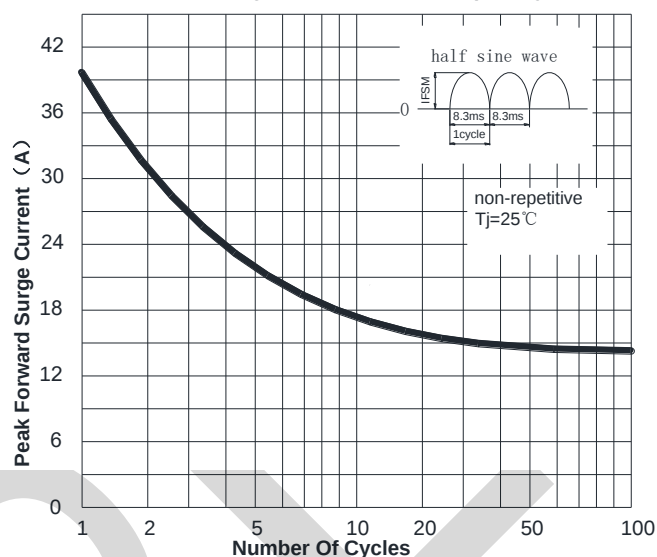


FIG3: Forward Voltage

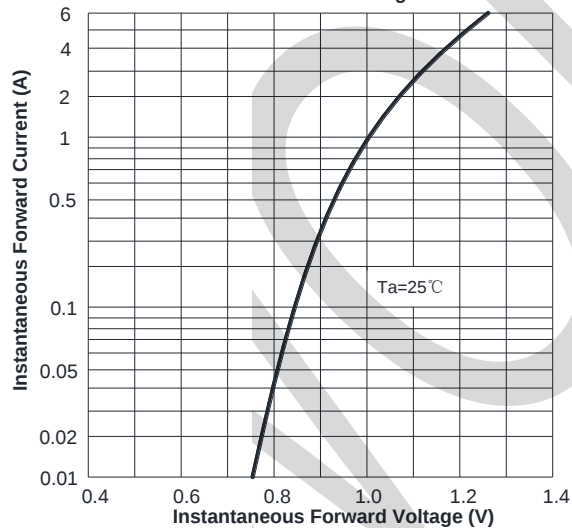
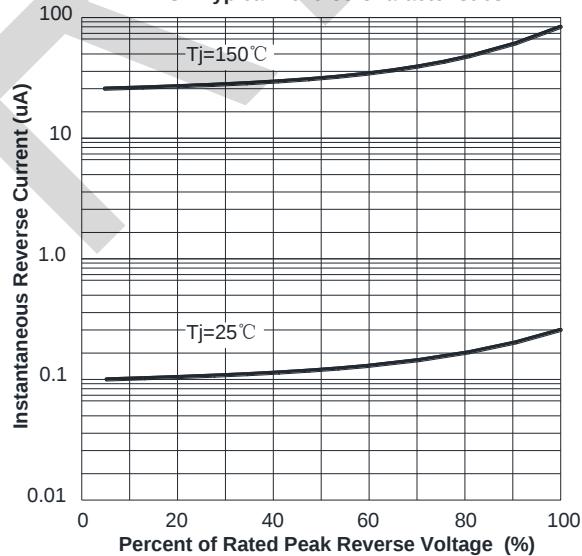


FIG4: Typical Reverse Characteristics



PACKAGE OUTLINE DIMENSIONS

Outline Dimensions: Dimensions

Case: DBS Series

Dimensions in millimeters

